

TO-220 Plastic-Encapsulated Transistors

2SB1185 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 2 \text{ W (Tamb=25°C)}$$

Collector current

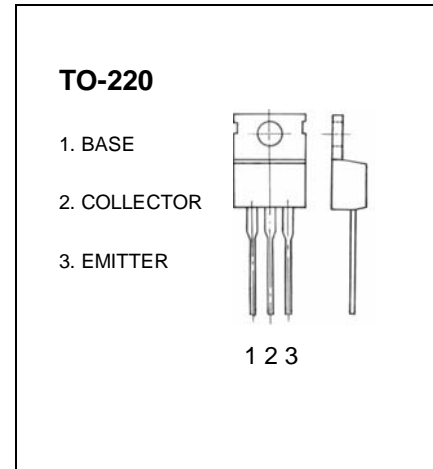
$$I_{CM}: -3 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-3\text{V}, I_C=-0.5\text{A}$	60		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}, f=30\text{MHz}$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		50		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F
Range	60-120	100-200	160-320
Marking			